

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	75mΩ@4.5V	1.2A
	90mΩ@2.5V	

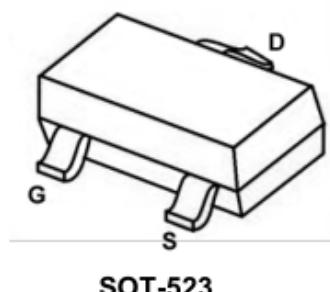
Feature

- TrenchFET Power MOSFET
- Excellent RDS(on) and Low Gate Charge

Applications

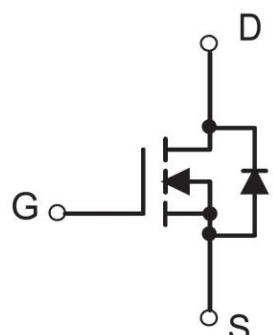
- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

Package

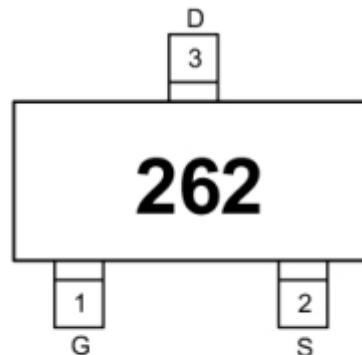


SOT-523

Circuit diagram



Marking



262 =Device Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	1.2	A
Pulsed Drain Current	I_{DM}	4.8	A
Maximum Power Dissipation	P_D	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

Electrical characteristics

($T_A=25^\circ\text{C}$, unless otherwise noted)

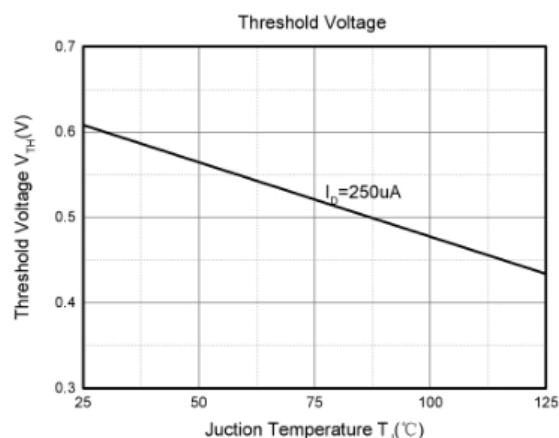
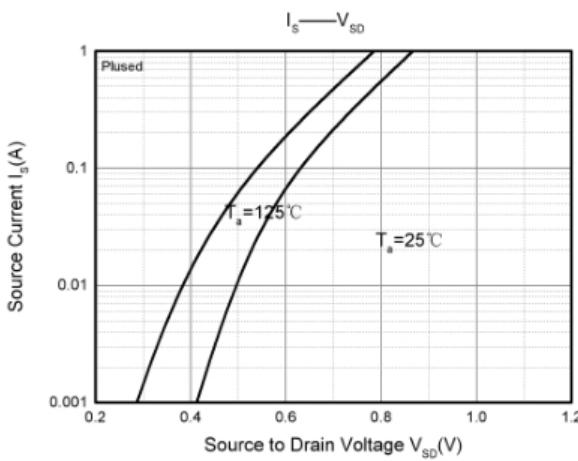
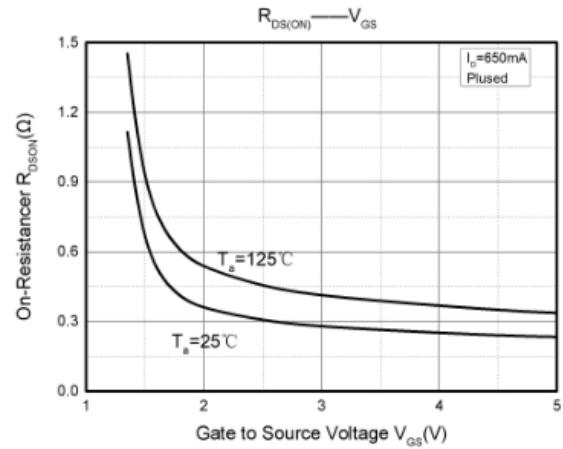
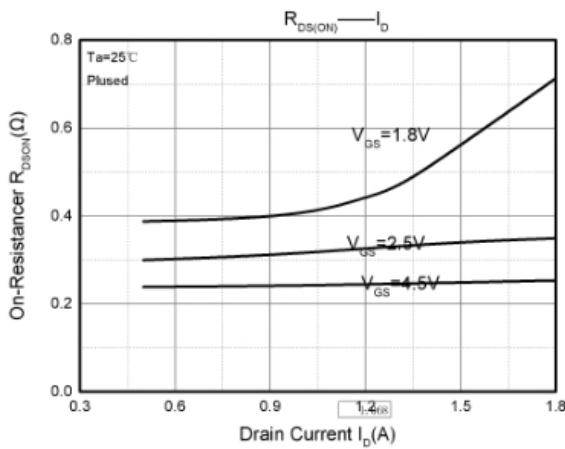
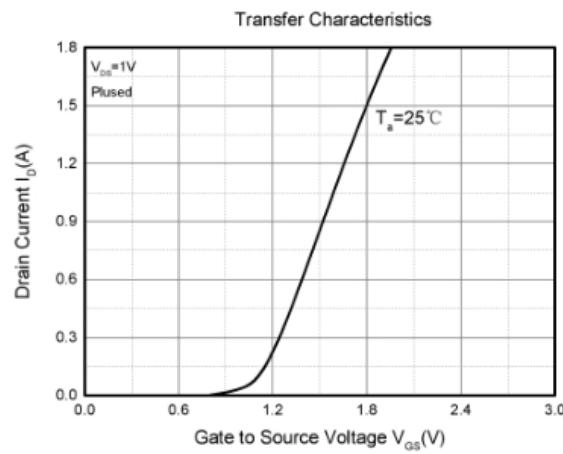
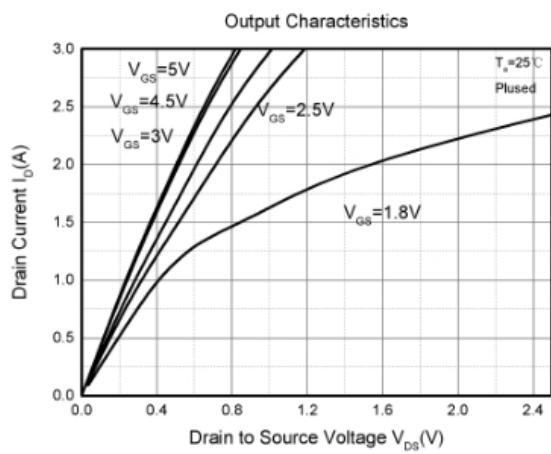
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10\text{V}, V_{DS} = 0\text{V}$			± 0.1	μA
Gate threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.4	0.65	1	V
Drain-source on-resistance	$R_{DS(\text{on})}$	$V_{GS} = 4.5\text{V}, I_D = 1\text{A}$		75	90	$\text{m}\Omega$
		$V_{GS} = 2.5\text{V}, I_D = 0.5\text{A}$		90	110	
Dynamic Characteristics⁴⁾						
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		220		pF
Output capacitance	C_{oss}			40		
Reverse transfer capacitance	C_{rss}			20		
Total gate charge	Q_g	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V}, I_D = 2\text{A}$		2.7		nC
Gate-source charge	Q_{gs}			0.4		
Gate-drain charge	Q_{gd}			0.5		
Switching Characteristics⁴⁾						
Turn-on Delay Time	$T_{d(on)}$	$V_{DD} = 10\text{V}, R_G = 6\Omega, V_{GEN} = 4.5\text{V}, R_L = 3.3\Omega$		2.3		nS
Turn-on Rise Time	T_r			3.1		
Turn-Off Delay Time	$T_{d(off)}$			20		
Turn-Off Fall Time	t_f			2.5		
Source-Drain Diode Characteristics⁴⁾						
Diode Forward voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$			1.2	V

Notes:

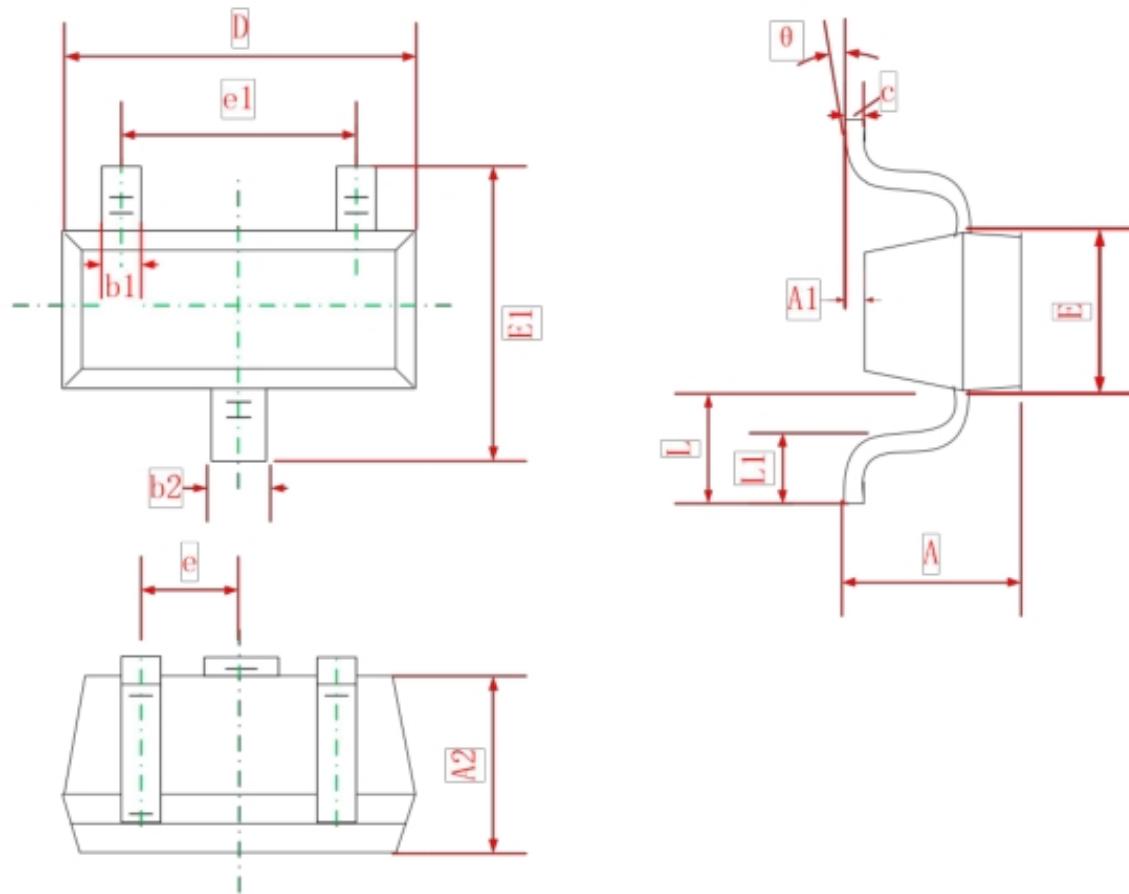
1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

2. These parameters have no way to verify.

Typical Characteristics



SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°